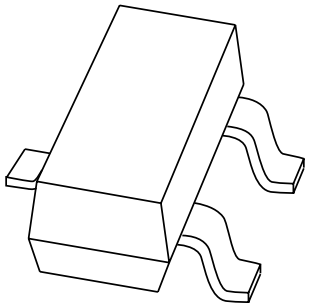
DATA SHEET



PMBT2907; PMBT2907A
PNP switching transistors

Product specification
Supersedes data of 1999 Apr 27

2004 Jan 16

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PNP switching transistors PMBT2907; PMBT2907A

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 60 V).

APPLICATIONS

- Switching and linear amplification.

DESCRIPTION

PNP switching transistor in a SOT23 plastic package.
NPN complements: PMBT2222 and PMBT2222A.

MARKING

TYPE NUMBER	MARKING CODE(1)
PMBT2907	*2B
PMBT2907A	*2F

Note

1. * = p : Made in Hong Kong.
   * = t : Made in Malaysia.
   * = W: Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

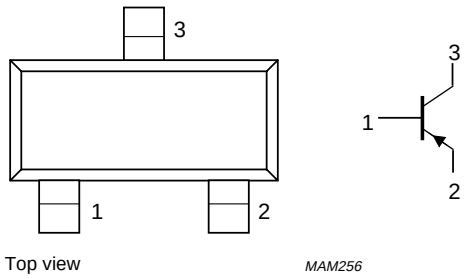


Fig.1 Simplified outline (SOT23) and symbol.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PMBT2907	–	plastic surface mounted package; 3 leads	SOT23
PMBT2907A	–	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–60	V
V_{CEO}	collector-emitter voltage	open base			
	PMBT2907		–	–40	V
	PMBT2907A		–	–60	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–600	mA
I_{CM}	peak collector current		–	–800	mA
I_{BM}	peak base current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

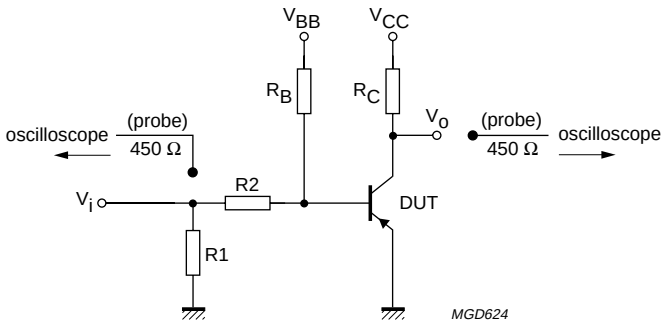
Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	I_E = 0; V_{CB} = –50 V			
	PMBT2907		–	–20	nA
	PMBT2907A		–	–10	nA
	collector-base cut-off current	I_E = 0; V_{CB} = –50 V; T_j = 125 °C			
	PMBT2907		–	–20	µA
	PMBT2907A		–	–10	µA
I_{EBO}	emitter-base cut-off current	I_C = 0; V_{EB} = –5 V	–	–50	nA
h_{FE}	DC current gain	I_C = –0.1 mA; V_{CE} = –10 V			
	PMBT2907		35	–	
	PMBT2907A		75	–	
	DC current gain	I_C = –1 mA; V_{CE} = –10 V			
	PMBT2907		50	–	
	PMBT2907A		100	–	
	DC current gain	I_C = –10 mA; V_{CE} = –10 V			
	PMBT2907		75	–	
	PMBT2907A		100	–	
	DC current gain	I_C = –150 mA; V_{CE} = –10 V	100	300	
	DC current gain	I_C = –500 mA; V_{CE} = –10 V			
	PMBT2907		30	–	
	PMBT2907A		50	–	
V_{CEsat}	collector-emitter saturation voltage	I_C = –150 mA; I_B = –15 mA	–	–400	mV
		I_C = –500 mA; I_B = –50 mA	–	–1.6	V
V_{BEsat}	base-emitter saturation voltage	I_C = –150 mA; I_B = –15 mA	–	–1.3	V
		I_C = –500 mA; I_B = –50 mA	–	–2.6	V
C_c	collector capacitance	$I_E = I_e$ = 0; V_{CB} = –10 V; f = 1 MHz	–	8	pF
C_e	emitter capacitance	$I_C = I_c$ = 0; V_{EB} = –2 V; f = 1 MHz	–	30	pF
f_T	transition frequency	I_C = –50 mA; V_{CE} = –20 V; f = 100 MHz	200	–	MHz
Switching times (between 10% and 90% levels); (see Fig.2)					
t_{on}	turn-on time	I_{Con} = –150 mA; I_{Bon} = –15 mA; I_{Boff} = 15 mA	–	40	ns
t_d	delay time		–	12	ns
t_r	rise time		–	30	ns
t_{off}	turn-off time		–	365	ns
t_s	storage time		–	300	ns
t_f	fall time		–	65	ns

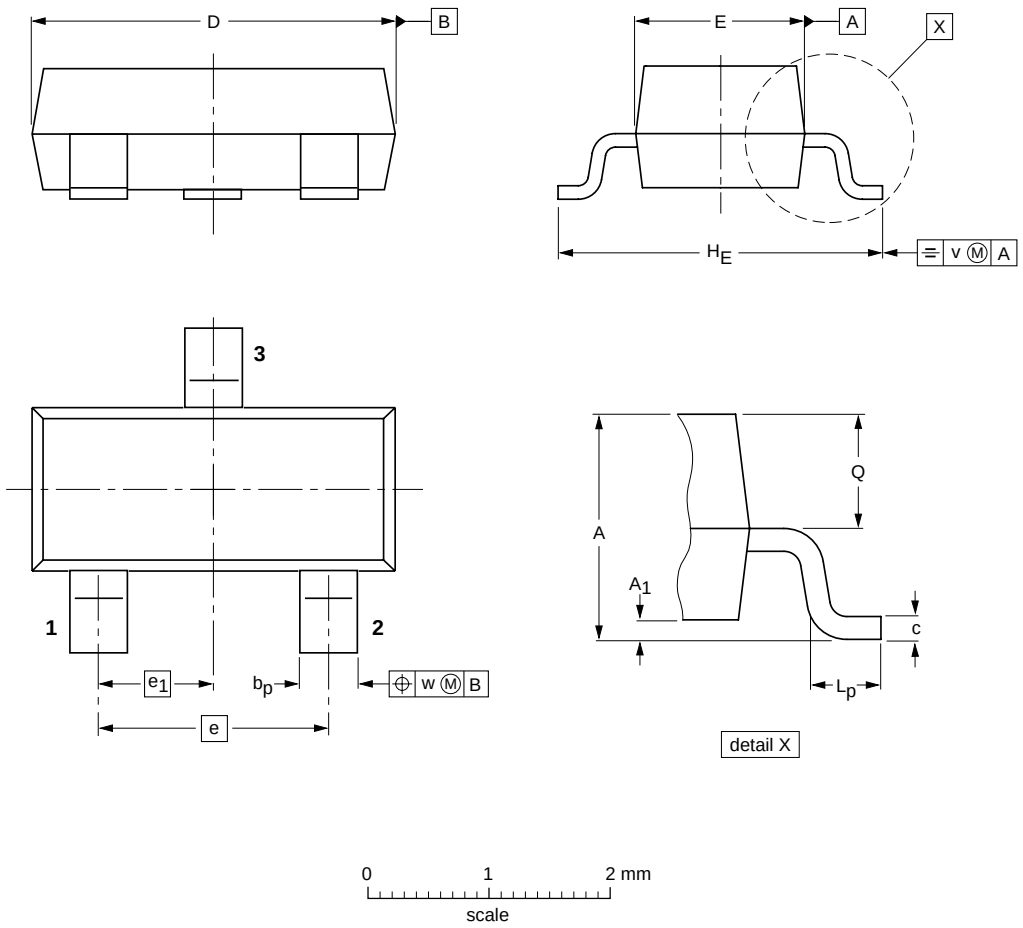


V_i = −9.5 V; T = 500 μs; t_p = 10 μs; $t_r = t_f \leq 3$ ns.
R1 = 68 Ω; R2 = 325 Ω; R_B = 325 Ω; R_C = 160 Ω.
V_{BB} = 3.5 V; V_{CC} = −29.5 V.
Oscilloscope: input impedance Z_i = 50 Ω.

Fig.2 Test circuit for switching times.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT23**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max.	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				~~97-02-28~~ 99-09-13

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS(1)	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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